11. (Original) The method of claim 9, further comprising:

preheating the underfill material after the carrier substrate is located adjacent the no-flow underfill material but before the interconnection elements are reflowed.

12. (Original) The method of claim 9, further comprising:

holding the microelectronic die with a chuck while the interconnection elements are being reflowed; and

releasing the chuck from the microelectronic die.

13. (Original) The method of claim 9, wherein the no-flow underfill material is preheated at a temperature between 30°C and 120°C.

14. (Original) The method of claim 13, wherein the interconnection elements are reflowed at a temperature of at least 183°C.

15. (Currently amended) A method of making a microelectronic assembly, comprising:

assembling a construction including a carrier substrate, a microelectronic die having an integrated circuit, interconnection elements between the carrier substrate and the microelectronic die, and a no-flow underfill material between the interconnection elements;

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subsequently heating the no-flow underfill material to a temperature below a reflowing temperature of the interconnection elements;

subsequently connecting the microelectronic die with a chuck; and

reflowing the interconnection elements by heating the interconnection elements while the microelectronic die is held with the chuck.

16. (Original) The method of claim 15, wherein the construction is assembled by dispensing the no-flow underfill material on the carrier substrate.

17. (Original) The method of claim 15, wherein the no-flow underfill material is preheated at a temperature between 30°C and 120°C.

18. (Original) The method of claim 17, wherein the interconnection elements are reflowed at a temperature of at least 183°C.